

MRH250.16

Thyristor/Diode module

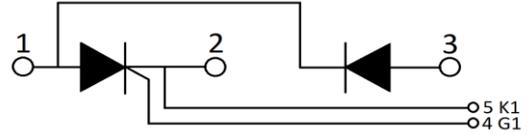
Features:

- International standard package
- High surge capability
- Glass passivated chip
- Simple mounting
- UL recognized, file no. E312789



Typical applications:

- Power converters
- Lighting control
- DC motor control and drives
- Heat and temperature control



Symbol	Characteristics	Test Conditions	Value			Unit
			Min	Typ	Max	
$V_{RSM/DSM}$	Non-repetitive reverse/forward blocking voltage	$T_j = 25^\circ\text{C}$			1700	V
$V_{RRM/DRM}$	Repetitive reverse/forward blocking voltage	$T_j = 25^\circ\text{C}$			1600	V
$I_T-I_{F(AV)}$	On-state/forward average current	180° half sine wave 50Hz			250	A
$I_T-I_{F(RMS)}$	RMS on-state current	$T_c = 83^\circ\text{C}$			390	A
I_{RRM} I_{DRM}	Repetitive peak current	at V_{DRM}/V_{RRM} $T_j = 125^\circ\text{C}$			50	mA
$I_{TSM}-I_{FSM}$	Surge non repetitive current	10ms half sine wave, $V_R = 0\text{V}$ $T_j = 25^\circ\text{C}$			7000	A
I^2t	I^2t for fusing coordination	10ms half sine wave, $T_j = 25^\circ\text{C}$			245000	A^2s
V_{TO}	Threshold voltage	$T_j = 125^\circ\text{C}$		0.86		V
r_T	On-state slope resistance	$T_j = 125^\circ\text{C}$			1.05	$\text{m}\Omega$
$V_{TM}-V_{FM}$	Peak on-state voltage	$T = 25^\circ\text{C}$; $I_F/I_T = 750\text{A}$			1.80	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM}$, $T_j = 125^\circ\text{C}$, linear voltage rise			1000	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of off-state current	$T_j = 125^\circ\text{C}$, $V_D = 50\% V_{DRM}$, $I_G = 150\text{mA}$, $di_G/dt = 0.1\text{A}/\mu\text{s}$			150	$\text{A}/\mu\text{s}$
I_{GT}	Gate trigger current	$V_A = 6\text{V}$, $T_j = 25^\circ\text{C}$			150	mA
V_{GT}	Gate trigger voltage				3	V
V_{GD}	Gate non-trigger voltage	$V_D = 67\% V_{DRM}$, $T_j = 125^\circ\text{C}$			0.25	V
I_H	Holding current	$T_j = 25^\circ\text{C}$		150		mA
I_L	Latching current	$T_j = 25^\circ\text{C}$		200		mA
t_{gt}	Turn on time	$T_j = 25^\circ\text{C}$		3		μs
$R_{th(j-c)}$	Thermal resistance junction to case	Single side cooled per chip			0.10	$^\circ\text{C}/\text{W}$
$R_{th(c-s)}$	Thermal resistance case to sink	Single side cooled per chip			0.05	$^\circ\text{C}/\text{W}$
V_{ISO}	Isolation voltage	50Hz, RMS, $t = 1\text{min}$, $I_{ISO} : 1\text{mA (MAX)}$		3000		V
F_M	Mounting torque - copper plate (M6)		4		6	N·m
	Mounting torque - terminal (M6)		4		6	N·m
T_{stg}	Storage Temperature		-40		125	$^\circ\text{C}$
T_j	Operating Temperature		-40		125	$^\circ\text{C}$
W_t	Weight			160		g
Outline	M42					

Performance Curves

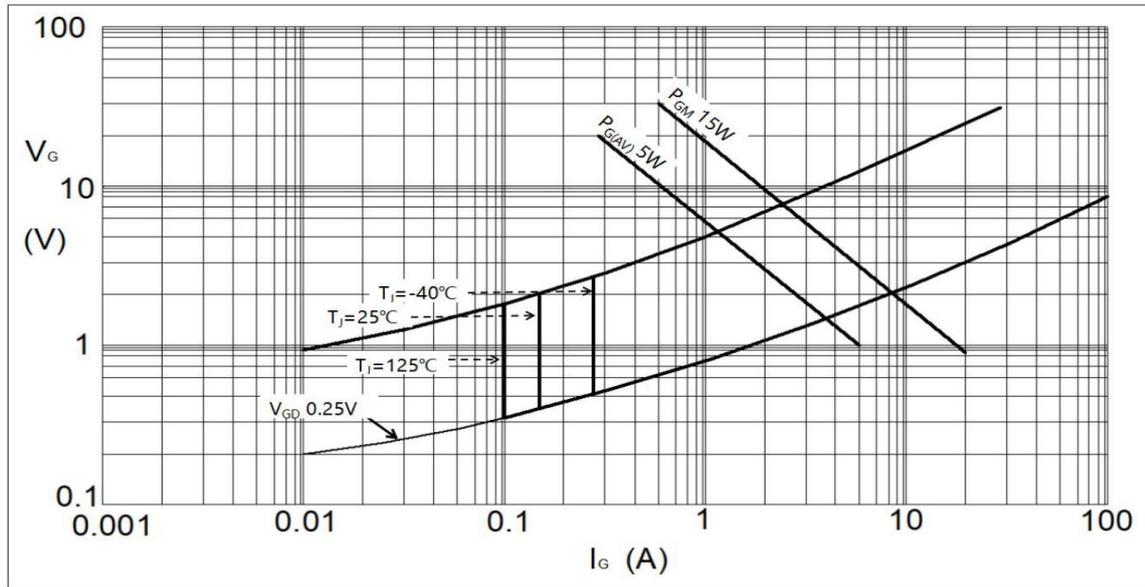


Fig1. Gate Trigger Characteristics

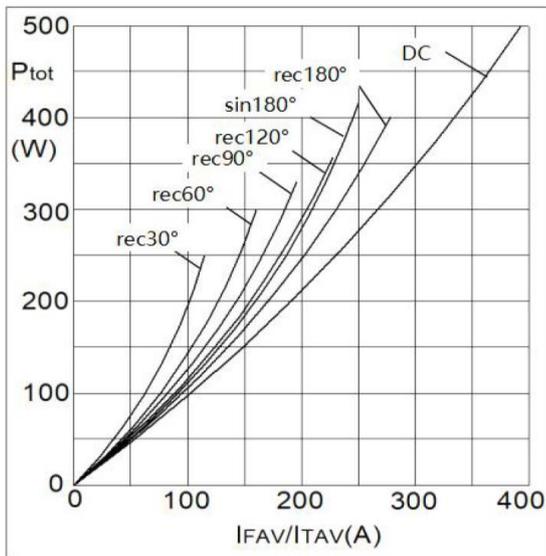


Fig2. Power Dissipation

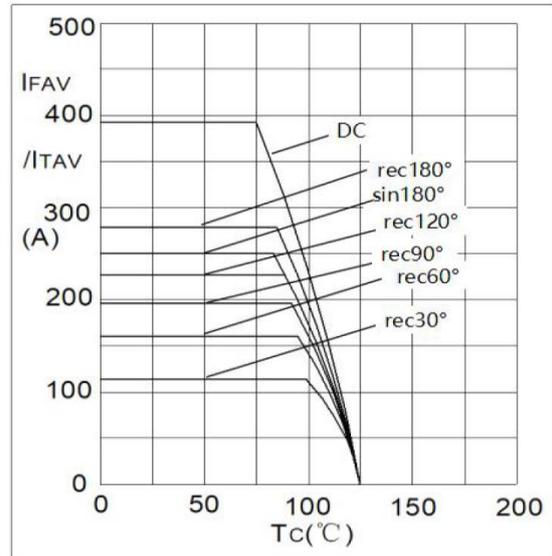


Fig3. Forward Current Derating Curve

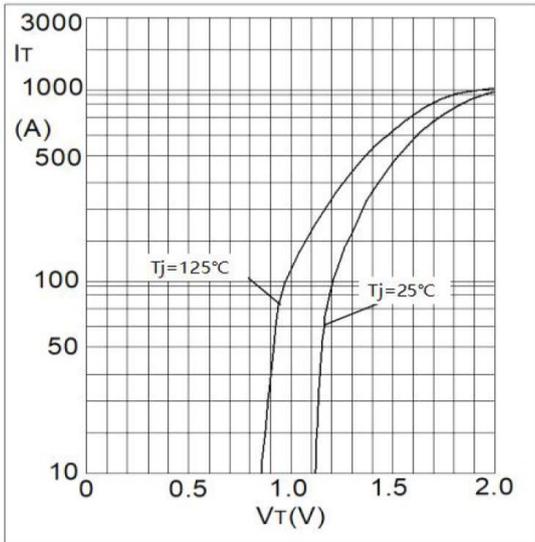


Fig4. Forward Characteristics

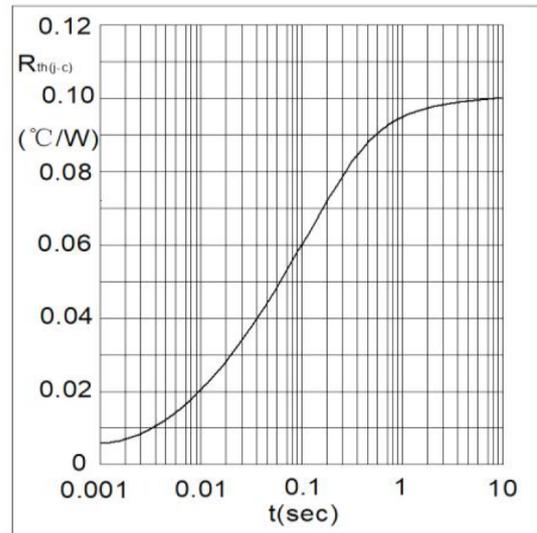


Fig5. Transient Thermal impedance

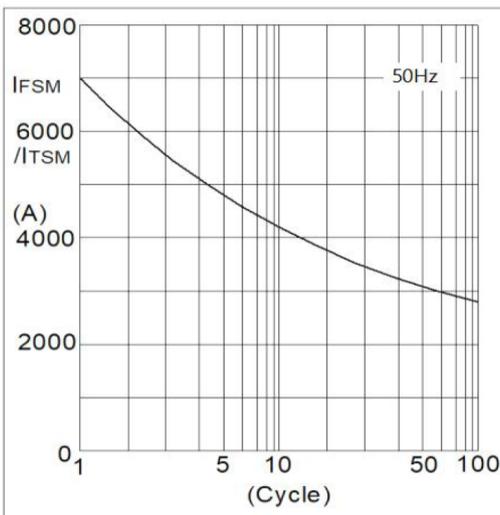
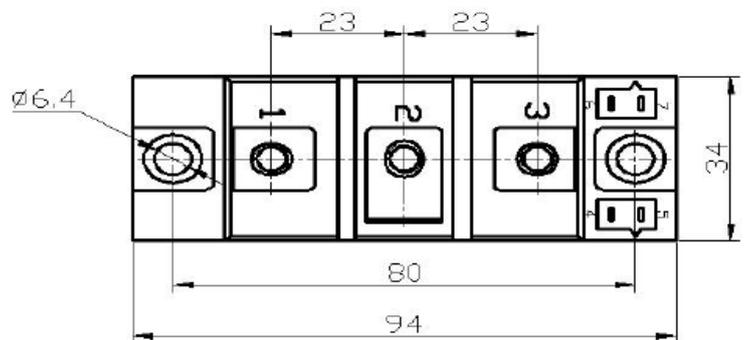
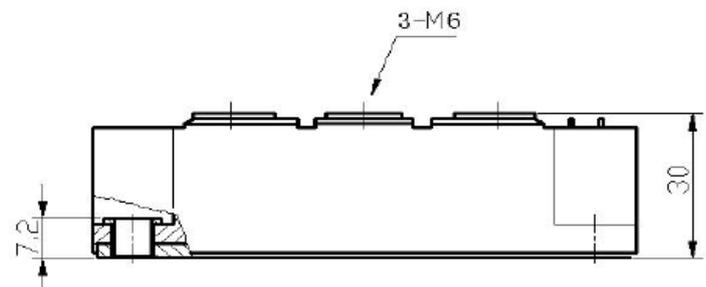


Fig6. Max Non-Repetitive Forward Surge Current



(dimensions in mm)

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